

# Theory of static structural properties, crystal stability, and Application to Si and Ge

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Citation Report

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1	Materials science: Cubic diamonds. Nature, 1983, 305, 102-102.	13.7	1
2	A pseudopotential approach to the lattice parameters for GaAs containing impurity elements. Physica Status Solidi (B): Basic Research, 1983, 119, 307-314.	0.7	20
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4	The electronic band structures for zincblende and wurtzite BeO. Journal of Physics C: Solid State Physics, 1983, 16, 3475-3480.	1.5	66
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